



## General Description

The AON6368 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable.

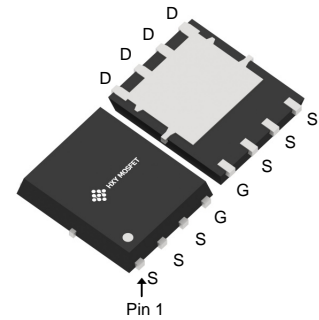
## General Features

$V_{DS} = 30V$   $I_D = 60A$

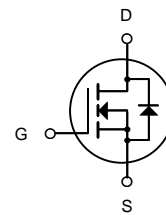
$R_{DS(ON)} < 5.8m\Omega @ V_{GS}=10V$

## Applications

Consumer electronic power supply Motor control  
Synchronous-rectification Isolated DC  
Synchronous-rectification applications



DFN5X6-8L



N-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AON6368	DFN5X6-8L	HXY MOSFET	5000

## Absolute Maximum Ratings (T<sub>c</sub> =25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	60	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	38	A
$I_{DM}$	Pulsed Drain Current	135	A
EAS	Single Pulse Avalanche Energy	29.8	mJ
$P_D @ T_C=25^\circ C$	Total Power Dissipation	30	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JC}$	Thermal Resistance from Junction-to-Ambient	4.6	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	50	°C/W



**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=20A$	---	4.4	5.8	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	6.9	9	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	67	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.7	---	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=15A$	---	8	---	nC
$Q_{gs}$	Gate-Source Charge		---	2.4	---	
$Q_{gd}$	Gate-Drain Charge		---	3.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=15A$	---	7.1	---	ns
$T_r$	Rise Time		---	40	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
$T_f$	Fall Time		---	6	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	814	---	pF
$C_{oss}$	Output Capacitance		---	498	---	
$C_{rss}$	Reverse Transfer Capacitance		---	41	---	
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	60	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
$t_{rr}$	Reverse Recovery Time	$I_F=20A, di/dt=100A/\mu s$ ,	---	15	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	25	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=24A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.



### Typical Characteristics



Fig.1 Typical Output Characteristics

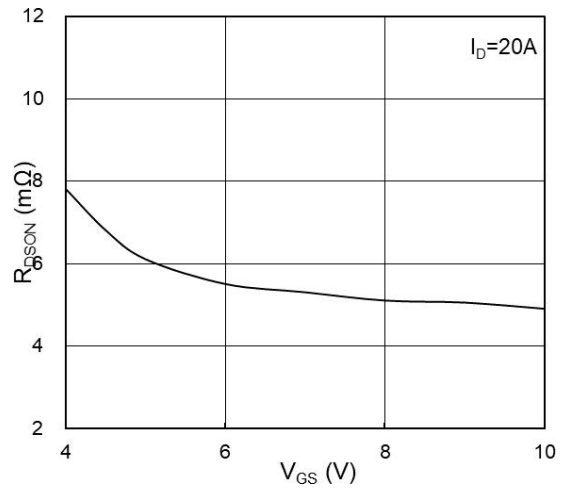


Fig.2 On-Resistance vs G-S Voltage

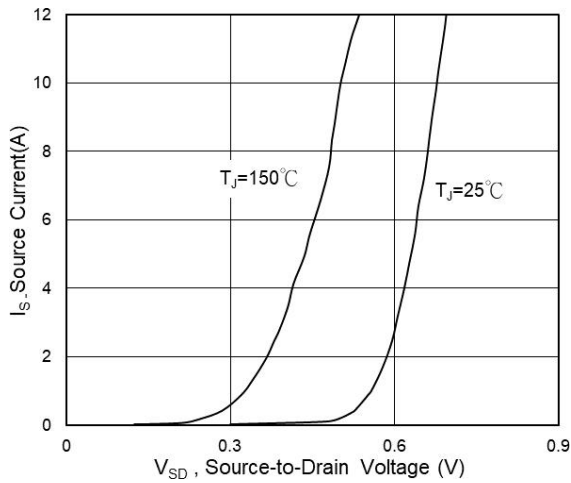


Fig.3 Source Drain Forward Characteristics

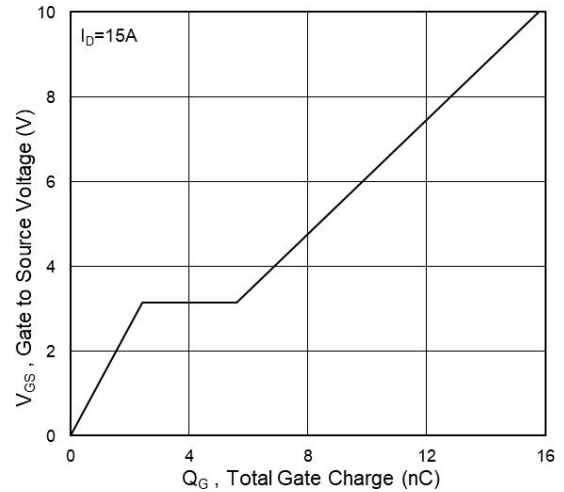


Fig.4 Gate-Charge Characteristics

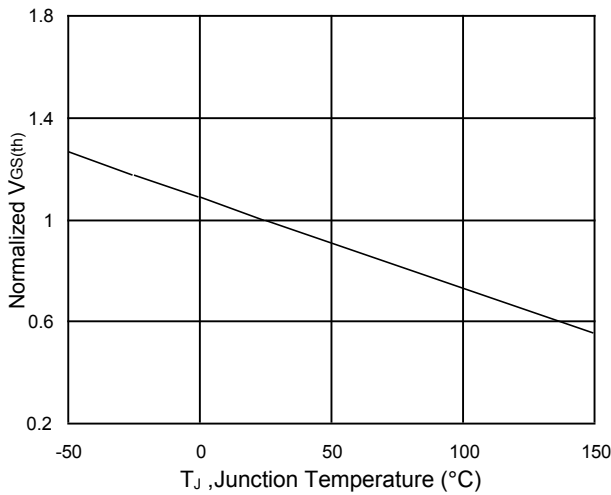


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$

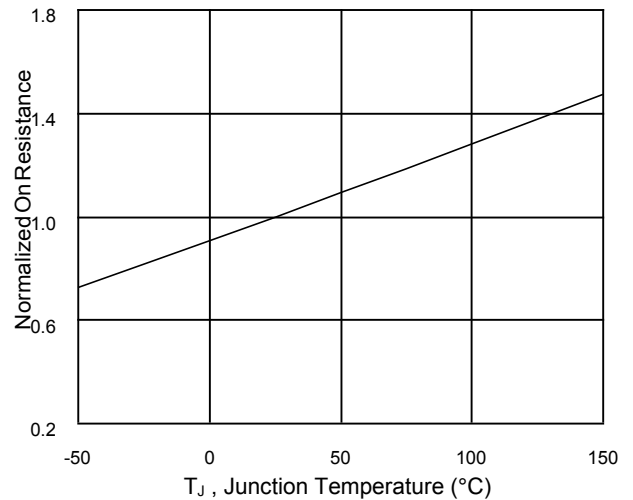


Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$

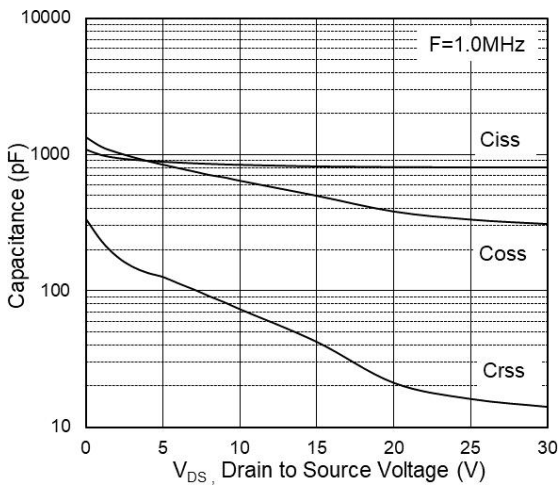


Fig.7 Capacitance

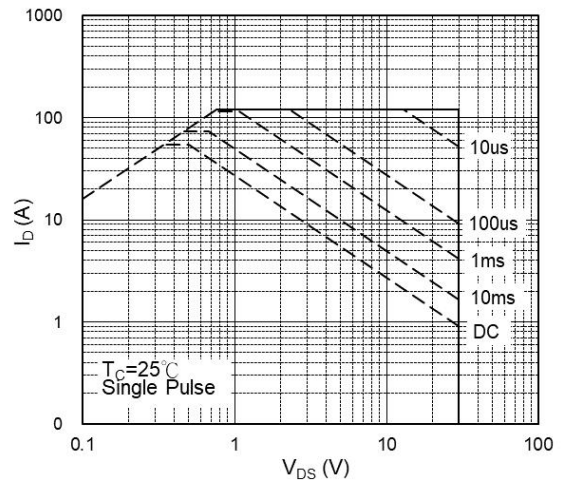


Fig.8 Safe Operating Area

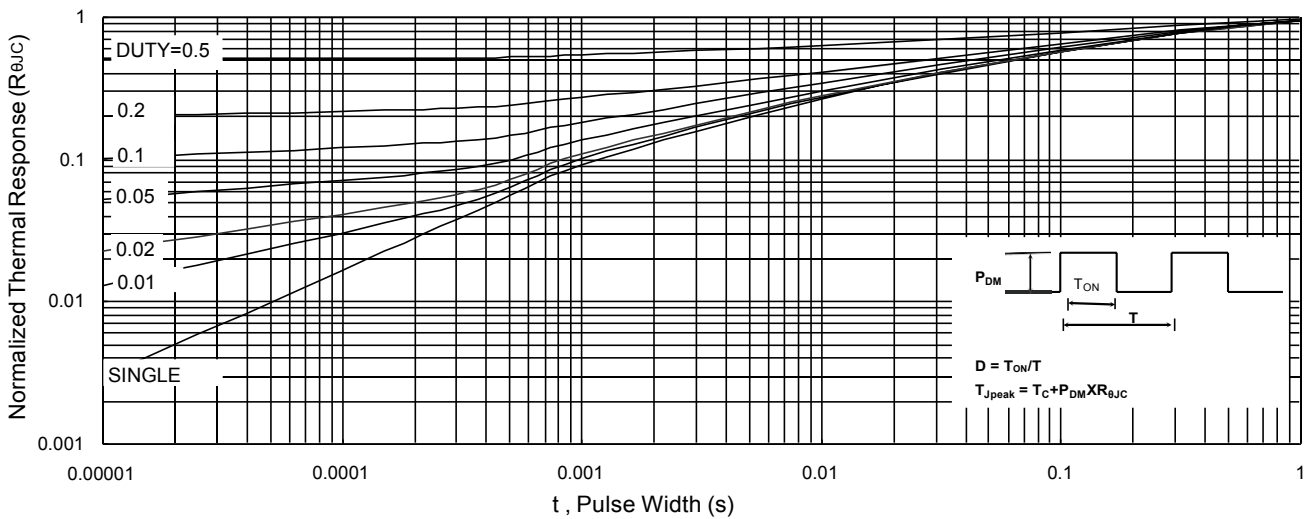


Fig.9 Normalized Maximum Transient Thermal Impedance

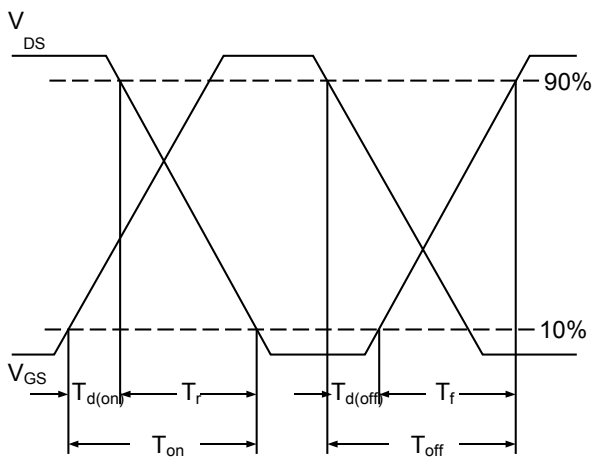


Fig.10 Switching Time Waveform

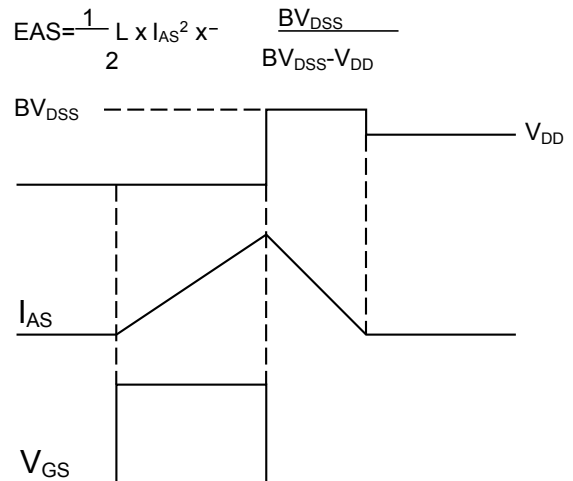
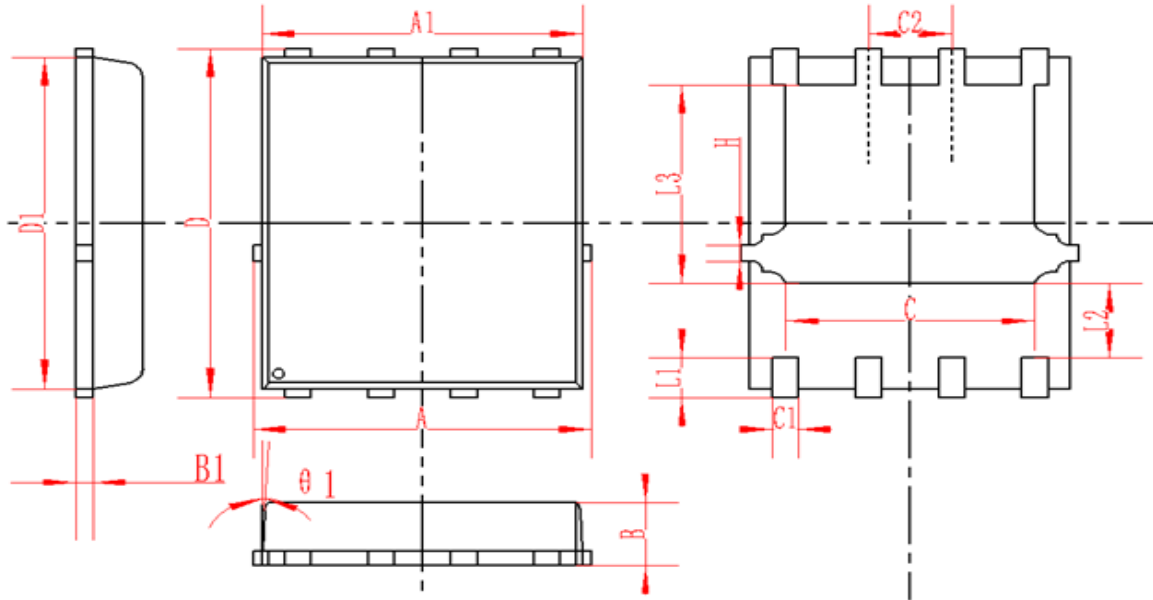


Fig.11 Unclamped Inductive Switching Waveform



### DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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